AMENDMENTS TO THE SPECIFICATION

Please amend the specification as follows:

At page 7, please insert the following new paragraph at line 6:

FIG. 6 illustrates an exemplary aspect of a device 600 according to the present invention.

At page 1, lines 21-25 and page 2, lines 1-13:

When, for example, Group III nitride compound semiconductors are applied to light-emitting devices, the Group III nitride compound semiconductors are direct transition type semiconductors having a wide emission spectrum range of from ultraviolet to red. The Group III nitride compound semiconductors are applied to light-emitting diodes (LEDs), laser diodes (LDs) and so on. Because each Group III nitride compound semiconductor has a wide band gap, there is an expectation that devices using Group III nitride compound semiconductors will operate more stably at a high temperature than devices using other semiconductors. For this reason, the application of Group III nitride compound semiconductors to transistors such as FETs has been developed actively. In addition, because each Group III nitride compound semiconductor contains no arsenic (As) as a main component, there is an expectation that Group III nitride compound semiconductors will be developed to various semiconductor devices for general purposes from an environmental aspect.

At page 7, lines 8-25, and page 8, lines 1-2:

The invention will be described below on the basis of a specific embodiment thereof. A Marlow-Das type pattern (shaped like a circular ring with a center point) of SiO_2 using photolithography was used as a metal electrode-forming pattern (FIG. 2). Here, the width d of the circular ring (SiO_2-forming portion) was set at 4, 8, 16 or 24 μm. Gallium nitride (GaN) was used as a Group III nitride compound semiconductor (e.g., 640). A 4 μm-thick layer of GaN (e.g., 640) was formed on a sapphire substrate (e.g., 650) using a face A (e.g., 635) as a principal surface with interposition of a low-temperature deposited buffer layer of aluminum nitride (AlN) (e.g., 645) by a metal organic chemical-vapor deposition method (MOCVD method). A 0.5 μm-thick layer of GaN doped with magnesium (Mg) to be formed as a p-type semiconductor (e.g., 630) was further formed on the GaN layer (e.g., 640). The hole density of the p-type GaN layer (e.g., 630) was $5x10^{17}$ cm^{-3}. Incidentally, the laminate composed of the sapphire substrate (e.g., 650), AlN (e.g., 645), GaN (e.g., 640) and p-type GaN (e.g., 630) is hereinafter referred to as "GaN" substrate (e.g., 660). Evaluation was carried out by measurement of contact resistance R_0 according to a current (I)-voltage (V) method and structural analysis of the metal film (e.g., 610) according to XRD.

At page 8, lines 3-13:

The GaN substrate (e.g., 660) having a p-type GaN (e.g., 630) surface cleaned with hydrochloric acid was placed in a chamber of an evaporation system. Then, on the GaN substrate (e.g., 660) heated to a temperature of 300° C, a 50 nm-thick metal layer (e.g., 610) was vapor-deposited by an electron beam vapor deposition method. The deposited metals were two kinds of metals, namely, platinum (Pt) and nickel (Ni).

Incidentally, a sample formed with the same film thickness without heating the GaN substrate (e.g., 660), that is, at room temperature (Comparative Example 1) and a sample heat-treated in a nitrogen (N_2) atmosphere at 300° C for 30 minutes after that (Comparative Example 2) were prepared as Comparative Examples.